

FRED Module

Fast Recovery Epitaxial Diode

$$V_{RRM} = 1200 \text{ V}$$

$$I_{FAVM} = 260 \text{ A}$$

$$t_{rr} = 400 \text{ ns}$$

Part number

MEA 250-12DA

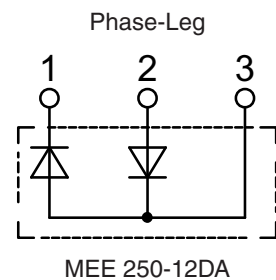
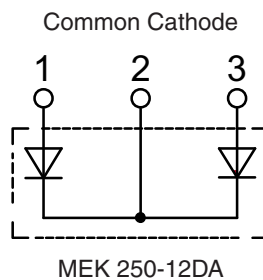
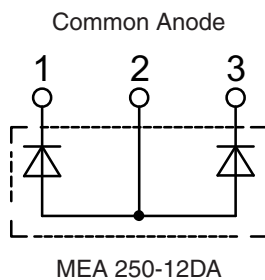
MEK 250-12DA

MEE 250-12DA



 E72873

Backside: isolated



Features / Advantages:

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Applications:

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Package: Y4-M6

- Isolation voltage: 3600 V~
- Industry standard outline
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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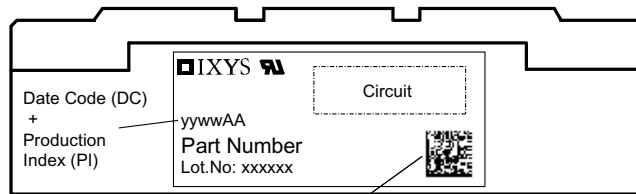


Diode				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
V_{RRM}	max. repetitive reverse		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			12	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			3	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 125^{\circ}\text{C}$			60	mA
V_F	forward voltage	$I_F = 150 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.69	V
			$T_{VJ} = 125^{\circ}\text{C}$			1.38	V
		$I_F = 260 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.80	V
			$T_{VJ} = 125^{\circ}\text{C}$			1.54	V
I_{FRMS}	RMS forward current		$T_C = 75^{\circ}\text{C}$			367	A
$I_{FAV}^{(1)}$	average forward current	$T_C = 75^{\circ}\text{C}$ rectangular, $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			260	A
V_{TO}	threshold voltage	for power-loss calculations only	$T_{VJ} = T_{VJM}$			1.16	V
r_T	slope resistance					1.46	m Ω
R_{thJC}	thermal resistance junction to case				0.085	0.143	K/W
R_{thCH}	thermal resistance junction to heatsink						K/W
P_{tot}	total power dissipation		$T_{VJ} = 25^{\circ}\text{C}$			875	W
I_{FSM}	max. surge forward current	$t = 10 \text{ ms}$ (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			2.40	kA
		$t = 8.3 \text{ ms}$ (60 Hz), sine				2.64	kA
		$t = 10 \text{ ms}$ (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			2.16	kA
		$t = 8.3 \text{ ms}$ (60 Hz), sine				2.38	kA
I^2t	I^2t value for fusing	$t = 10 \text{ ms}$ (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			28.8	kA ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine				29.3	kA ² s
		$t = 10 \text{ ms}$ (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			23.3	kA ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine				23.8	kA ² s
t_{rr}	max. reverse recovery current	$I_F = 250 \text{ A}; -di_F/dt = 400 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		200	250	ns
			$T_{VJ} = 100^{\circ}\text{C}$		400	500	ns
I_{RM}	reverse recovery time	$V_R = 600 \text{ V}; L \leq 0.05 \mu\text{H}$	$T_{VJ} = 25^{\circ}\text{C}$		44	52	A
			$T_{VJ} = 100^{\circ}\text{C}$		68	80	A

⁽¹⁾ I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$

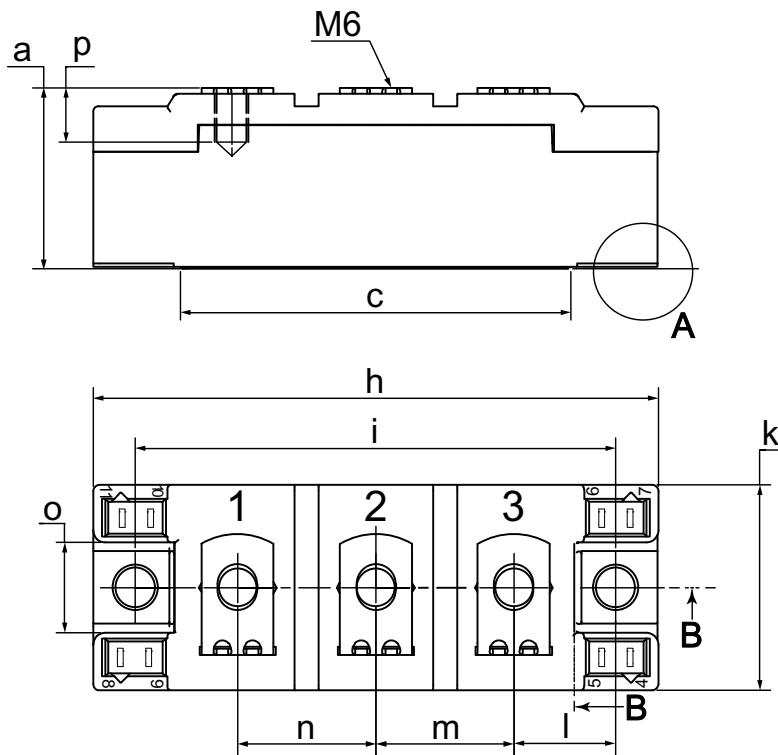


Package Y4-M6				Ratings		
Symbol	Definitions	Conditions		min.	typ.	max.
I_{RMS}	RMS current	per terminal				300 A
T_{VJ}	virtual junction temperature			-40		150 °C
T_{op}	operation temperature			-40		125 °C
T_{stg}	storage temperature			-40		125 °C
Weight					126	g
M_D	mounting torque			2.25		2.75 Nm
M_T	terminal torque			4.5		5.5 Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600 3000		V V

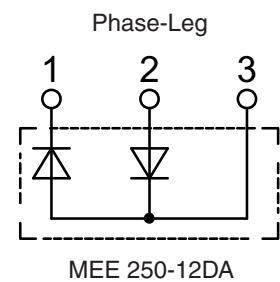
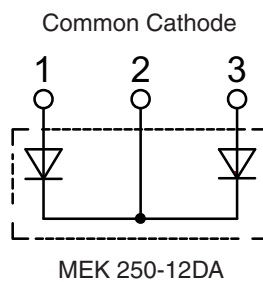
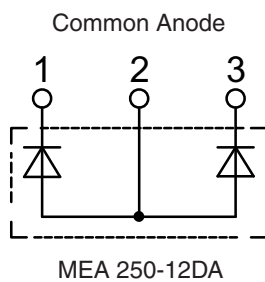
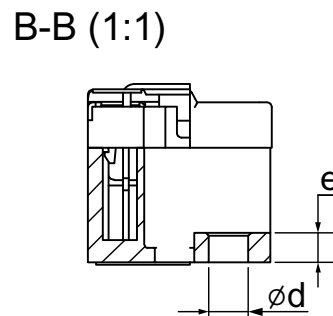
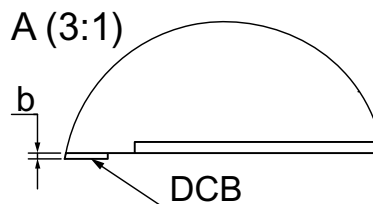


Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MEA 250-12DA	MEA 250-12DA	Box	36	464678
Standard	MEK 250-12DA	MEK 250-12DA	Box	36	464627
Standard	MEE 250-12DA	MEE 250-12DA	Box	36	464694

Outlines Y4-M6


Dim.	min [mm]	max [mm]	min [inch]	max [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	



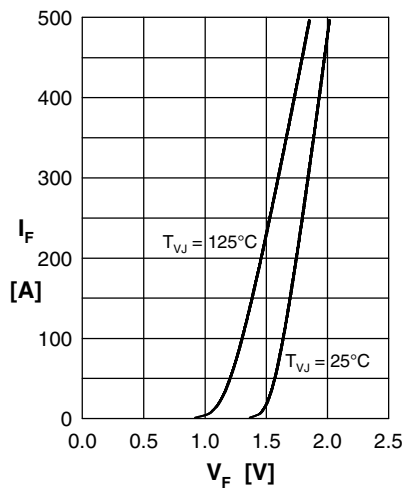
Curves


Fig. 1 Typ. forward current I_F vs. voltage drop V_F per leg

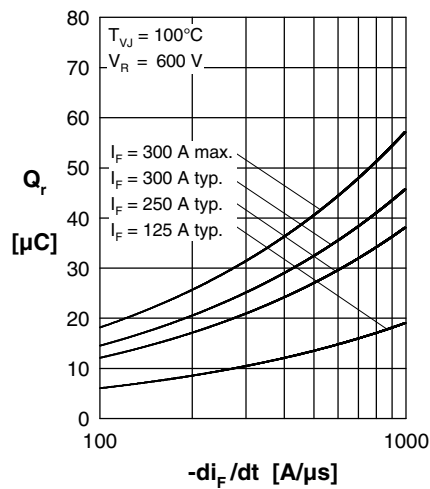


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

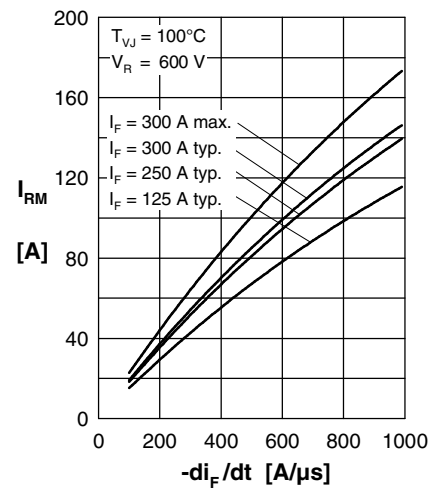


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

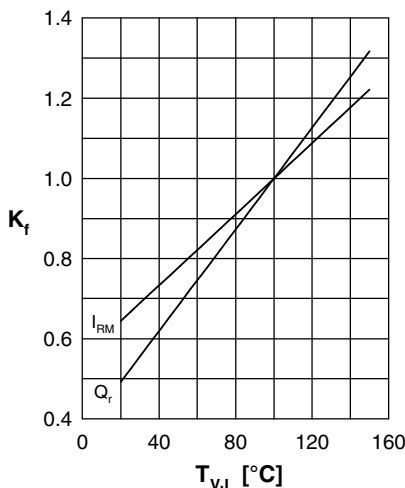


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus junction temperature T_{VJ}

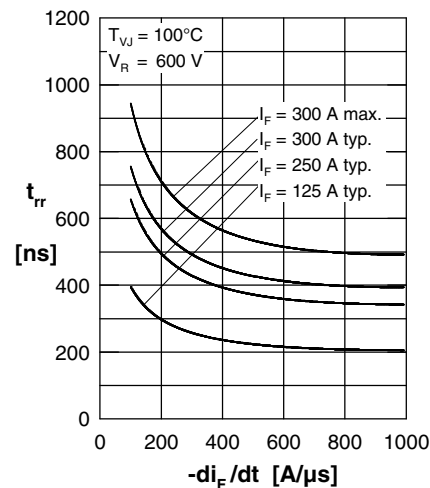


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

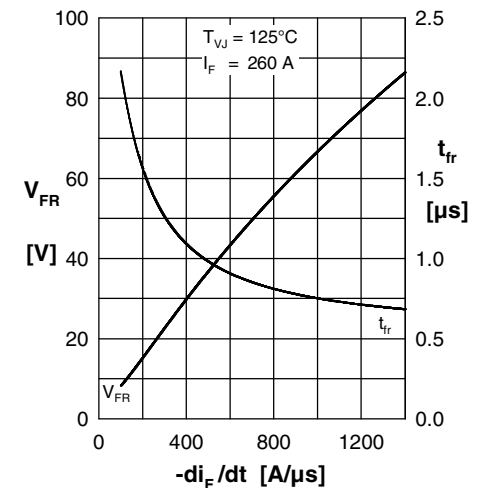


Fig. 6 Typ. peak forward voltage V_{FR} and t_{tr} versus $-di_F/dt$

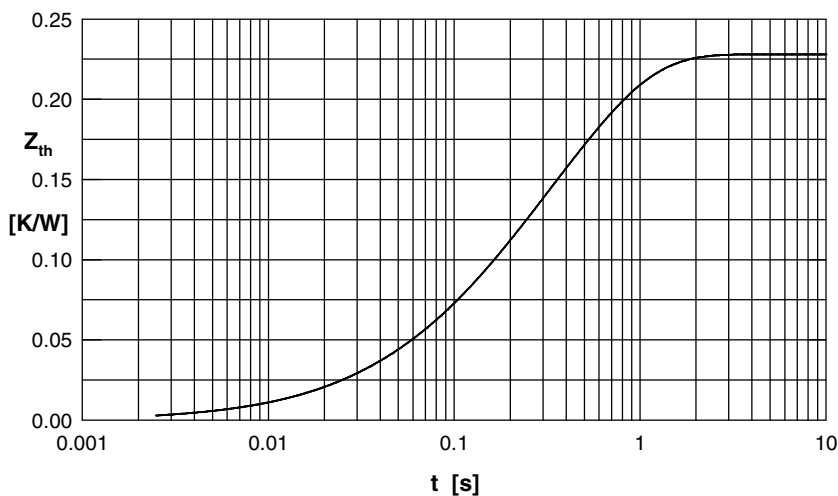


Fig. 7 Typ. transient thermal impedance junction to heatsink

Constants for Z_{thJS} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.002	0.08
2	0.008	0.024
3	0.054	0.112
4	0.164	0.464